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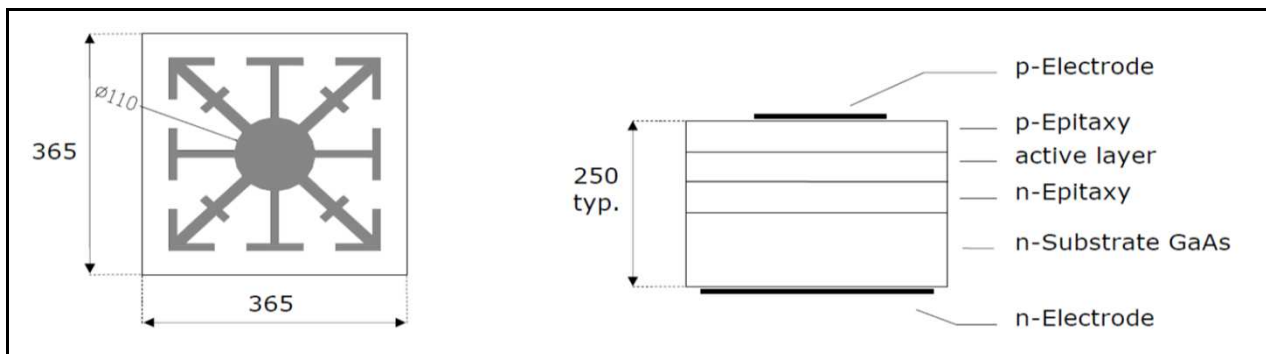
Data Sheet

LED Chip Infrared

EOLC-980-17-1

Rev. 01, 2017

Radiation	Type	Electrodes
Infrared	GaAs, MQW	P (anode) up



Chip thickness: typ. 250 μm, electrodes / metallization - Au alloy

Maximum ratings

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)	$T_{amb}=25^{\circ}\text{C}$	I_F	100	mA
Reverse voltage		V_R	5	V
Storage and operating temp. range	for bare chips	T_{amb}	-40...+100	$^{\circ}\text{C}$
Storage temperature range	for chips on blue tape	T_{stg}	+5...+35	$^{\circ}\text{C}$
Junction temperature		T_J	+125	$^{\circ}\text{C}$

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=20\text{ mA}$	V_F		1.25	1.45	V
Reverse current	$V_R=5\text{ V}$	I_R			10	μA
Radiant power*	$I_F=20\text{ mA}$	Φ_e		2		mW
Peak wavelength	$I_F=20\text{ mA}$	λ_p		980		nm
FWHM	$I_F=20\text{ mA}$	$\Delta\lambda_{0.5}$		35		nm
Switching time	$I_F=20\text{ mA}$	t_r, t_f		15; 20		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 044



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.